



September 2008

FDZ391P

P-Channel 1.5 V PowerTrench[®] Thin WL-CSP MOSFET

-20 V, -3 A, 85 mΩ

Features

- Max $r_{DS(on)}$ = 85 mΩ at $V_{GS} = -4.5$ V, $I_D = -1$ A
- Max $r_{DS(on)}$ = 123 mΩ at $V_{GS} = -2.5$ V, $I_D = -1$ A
- Max $r_{DS(on)}$ = 200 mΩ at $V_{GS} = -1.5$ V, $I_D = -1$ A
- Occupies only 1.5 mm² of PCB area
- **Ultra-thin package:** less than 0.4 mm height when mounted to PCB
- RoHS Compliant

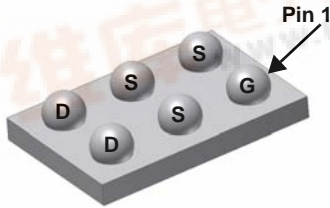


General Description

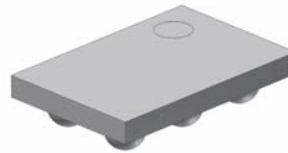
Designed on Fairchild's advanced 1.5 V PowerTrench process with state of the art "low pitch" **Thin** WLCSP packaging process, the FDZ391P minimizes both PCB space and $r_{DS(on)}$. This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge, and low $r_{DS(on)}$.

Applications

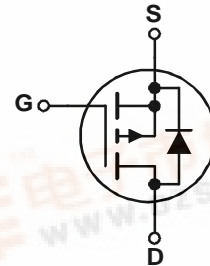
- Battery management
- Load switch
- Battery protection



BOTTOM



TOP



MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Rated Value	Units
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	Drain Current -Continuous	$T_A = 25$ °C (Note 1a)	A
	-Pulsed		
P_D	Power Dissipation	$T_A = 25$ °C (Note 1a)	W
	Power Dissipation	$T_A = 25$ °C (Note 1b)	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Rated Value	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	
			133

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
6	FDZ391P	WL-CSP Thin	7"	8 mm	5000 units

FDZ391P P-Channel 1.5V PowerTrench[®] WL-CSP MOSFET



Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-12		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}$, $V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{ V}$, $V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250\text{ }\mu\text{A}$	-0.4	-0.6	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		2		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = -4.5\text{ V}$, $I_D = -1\text{ A}$		74	85	m Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -1\text{ A}$		90	123	
		$V_{GS} = -1.5\text{ V}$, $I_D = -1\text{ A}$		140	200	
		$V_{GS} = -4.5\text{ V}$, $I_D = -1\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		100	123	
$I_{D(on)}$	On to State Drain Current	$V_{GS} = -4.5\text{ V}$, $V_{DS} = -5\text{ V}$	-10			A
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}$, $I_D = -1\text{ A}$		7		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		800	1065	pF
C_{oss}	Output Capacitance			155	205	pF
C_{rss}	Reverse Transfer Capacitance			90	135	pF
R_g	Gate Resistance		$f = 1\text{ MHz}$		9	

Switching Characteristics

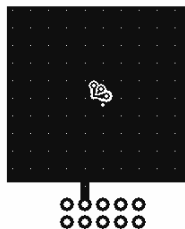
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10\text{ V}$, $I_D = -1\text{ A}$ $V_{GS} = -4.5\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		11	20	ns
t_r	Rise Time			10	20	ns
$t_{d(off)}$	Turn-Off Delay Time			50	80	ns
t_f	Fall Time			30	48	ns
Q_g	Total Gate Charge	$V_{GS} = -4.5\text{ V}$		9	13	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = -10\text{ V}$ $I_D = -1\text{ A}$		1		nC
Q_{gd}	Gate to Drain "Miller" Charge			2		nC

Drain-Source Diode Characteristics

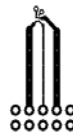
I_S	Maximum continuous Drain-Source Diode Forward Current			-1.1	A
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = -1.1\text{ A}$ (Note 2)	-0.7	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F = -1\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		21	ns
Q_{rr}	Reverse Recovery Charge			5	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 65 $^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper.



b. 133 $^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

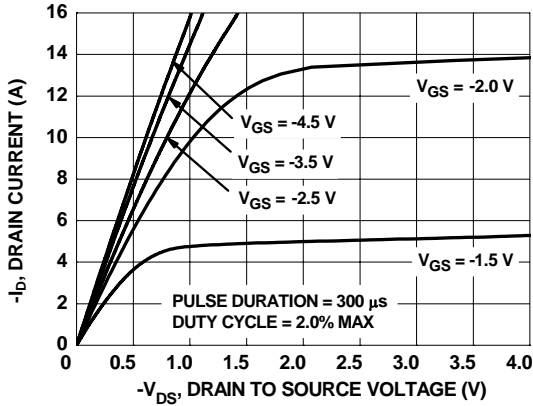


Figure 1. On Region Characteristics

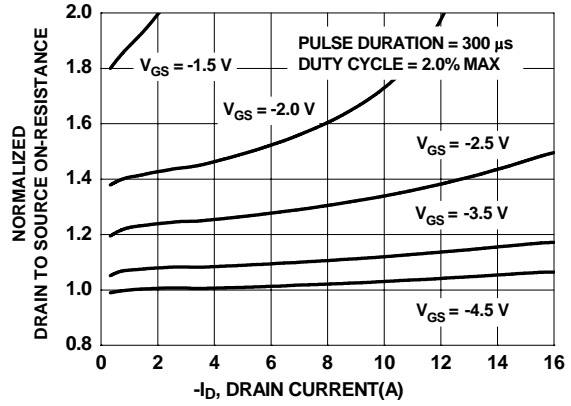


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

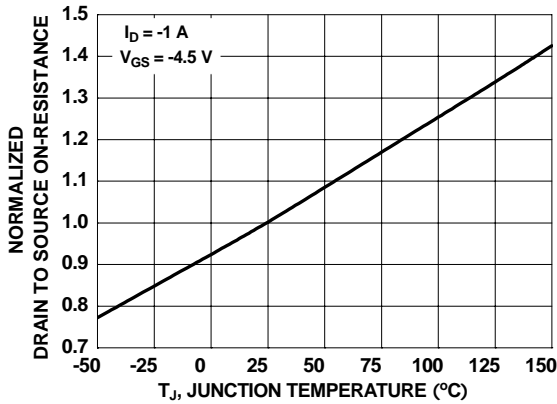


Figure 3. Normalized On Resistance vs Junction Temperature

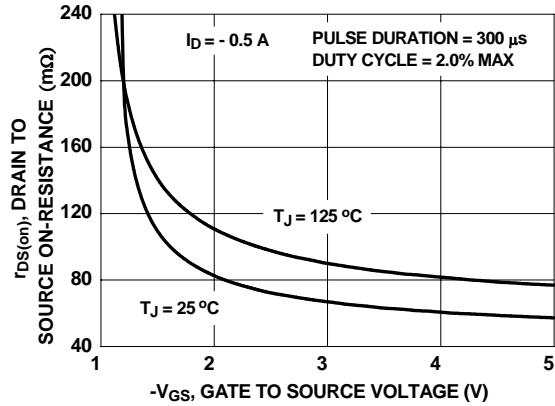


Figure 4. On-Resistance vs Gate to Source Voltage

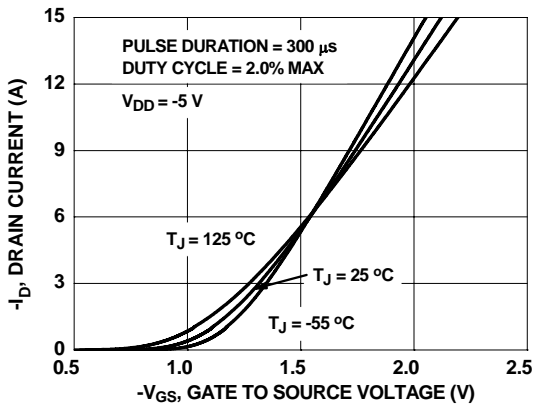


Figure 5. Transfer Characteristics

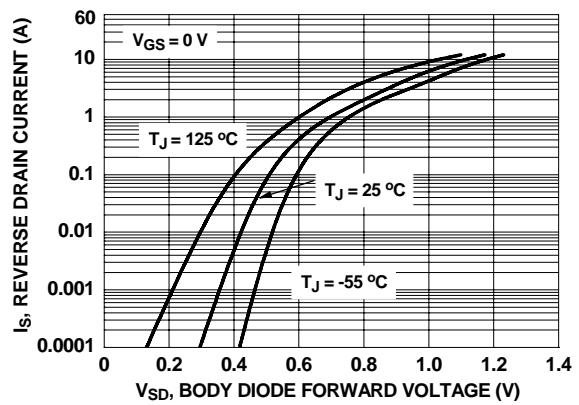


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

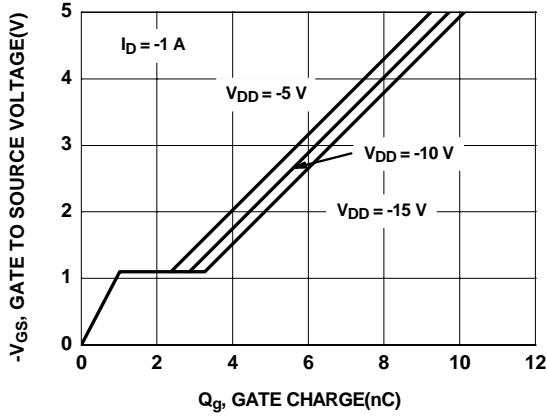


Figure 7. Gate Charge Characteristics

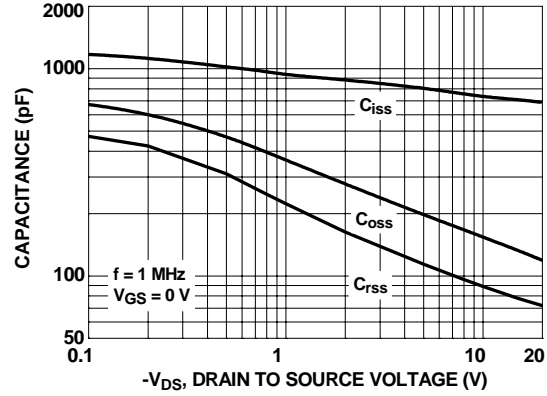


Figure 8. Capacitance vs Drain to Source Voltage

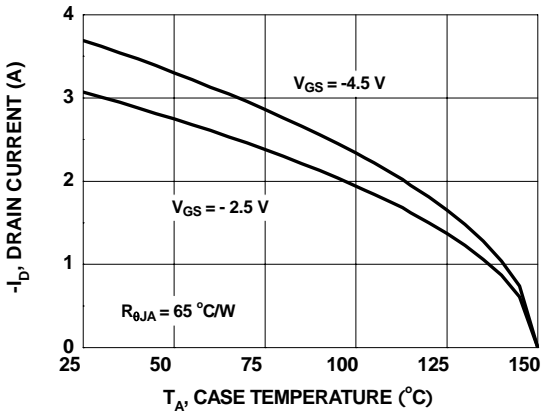


Figure 9. Maximum Continuous Drain Current vs Ambient Temperature

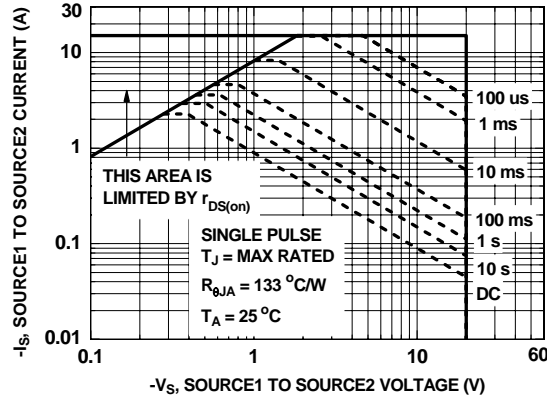


Figure 10. Forward Bias Safe Operating Area

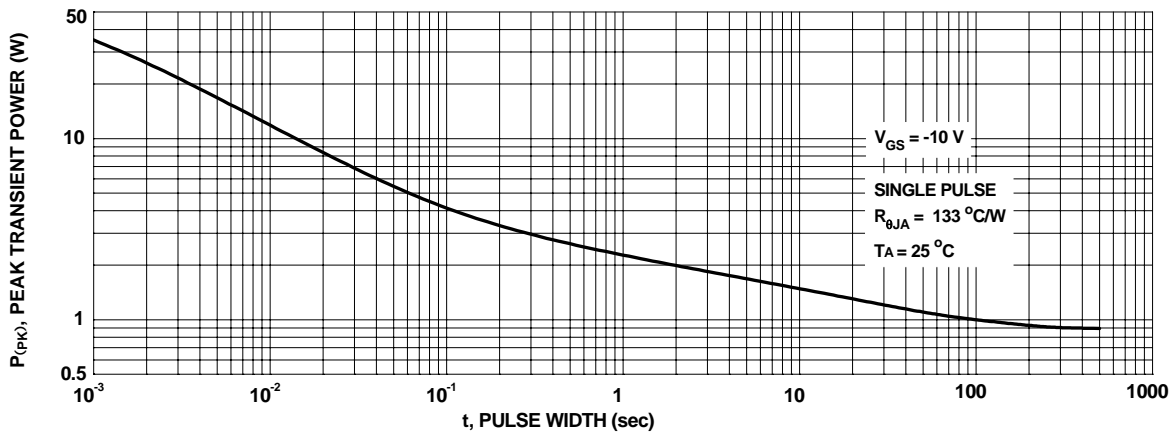
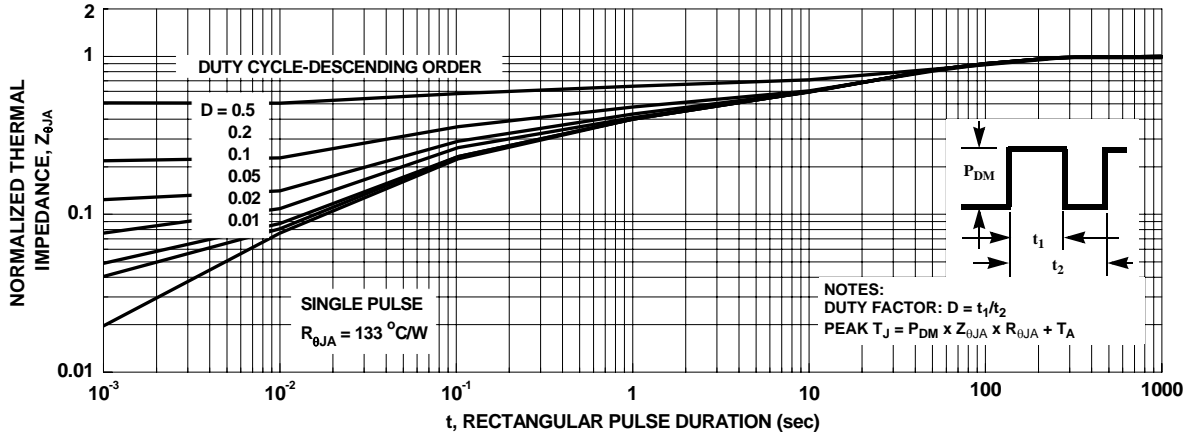
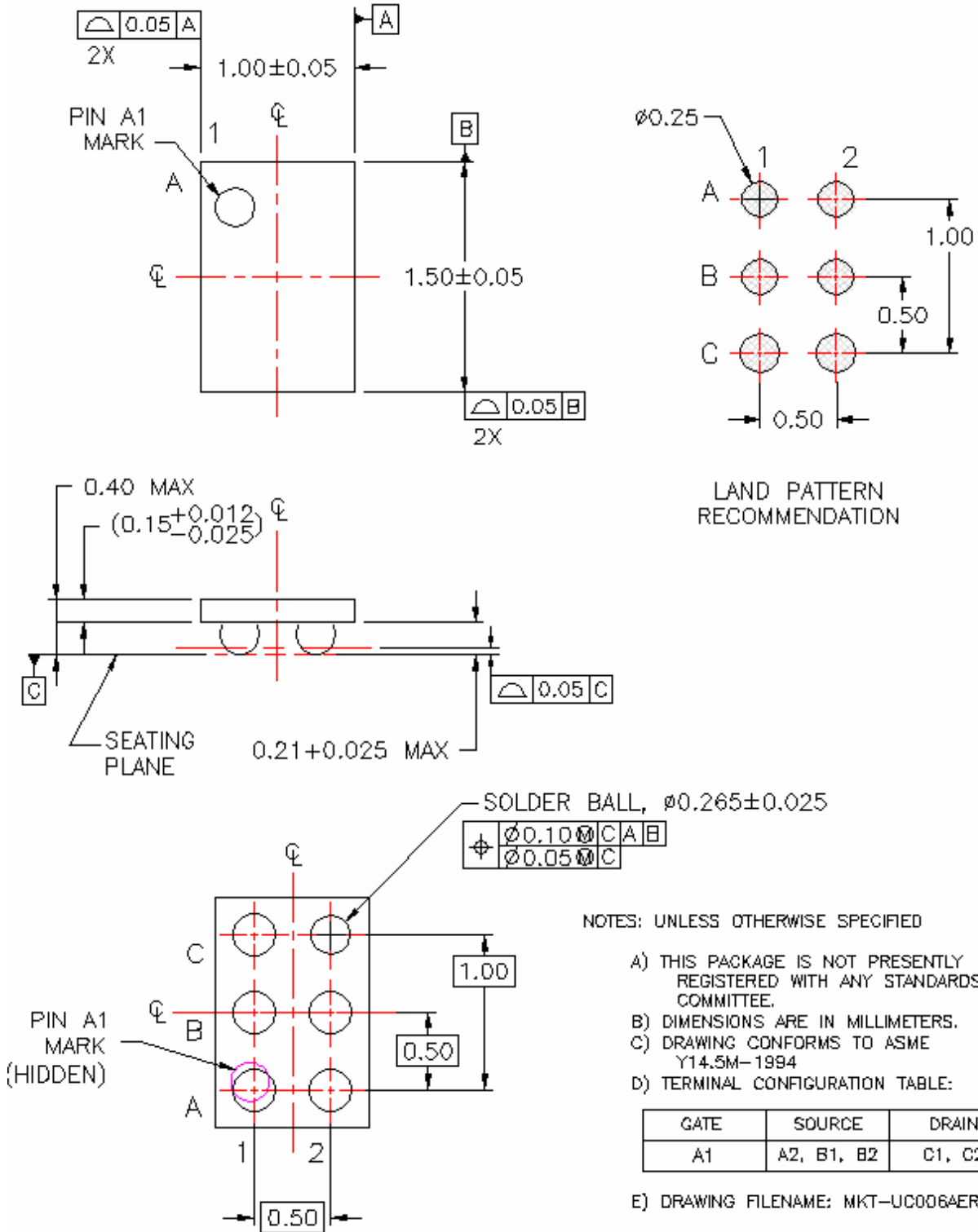


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted





Dimensional Outline and Pad Layout







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